. Department of Commerce, Patent and Trademark Office					Atty Docket		Serial No.		
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INFORMATION DISCLOSURE STATEMENT BY APPLICANT					Applicant(s)		4		
INFORMA	ATION I	Use several sheets if	necessary)		Daniel C. Guterman et al.				
IPE	(Use several sheets if			Filing Date		Group		
37					October 31,	2001	28177 3		
2 2 2002			LLC D	atent Documents			7)		
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YANDEMARKS IIITIA		Document Number	Date	Name	Class	Subclass	3		
Illrai -	AA	4,173,766	11/6/79	Hayes					
20	AB	4,527,257	7/2/85	Cricchi					
+	AC	4,622,656	11/11/86	Kamiya et al.					
		4,870,470	9/26/89	Bass, Jr. et al.					
13	AE	5,043,940	8/27/91	Harari					
7	AF	5,070,032	12/3/91	Yuan et al.		- E			
77	AG	5,095,344	3/10/92	Harari		CHAN	3 1		
	AH	5,168,334	12/1/92	Mitchell et al.			77 77		
77	Al	5,172,338	12/15/92	Mehrotra et al.			1 N		
1	AJ	5,313,421	5/17/94	Guterman et al.		2 14			
	AK	5,315,541	5/24/94	Harari et al.		in the second			
f'>	AK L	3,515,5 1	Forei	gn Patent Documents			Translatio		
	Γ	Document	Date	Country	Class	Subclass	Yes N		
	A.T.	EP 1 073 120 A2	1/31/01	Europe					
17 1	AL	EP 1 091 418 A2	4/11/01	Europe					
	AM	EP 1 096 505 A1	5/2/01	Europe					
	AN	EF 1070 303 711							
	AO								
	AP	OTHER A	ART (Includin	g Author, Title, Date, F	Pertinent Pages	, Etc.)			
· 	AQ		M. A novel l	localized trapping, 2-bit local seed trapping, 2-bit lober 2000, pp. 543-5.	nonvolatile m	emory cell," <u>IEI</u>	EE Electron Devic		
1		Letters, vol. 21, n	. 11, 110 (call for a cemi	-conductor disk	application," IEE		
	AR	Lournal of Solid	State Circuits.	ith a MONOS memory, vol. 26, no. 4, April 19	•				
. 25	AS	Chan et al., "A to Letters, vol. EDI	rue single-trar 8, no. 3, Ma	nsistor oxide-nitride-oxi arch 1987, pp. 93-95.	de EEPROM o	levice," <u>IEEE E</u>	lection Device		
ı		_ Ka		isidered $\frac{1}{15}$ or not citation is in conude copy of this form w					
	<i></i>		1 Date Con				1' 41		

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•	5/	U.S. FC		Class	Subclass-		Appropriate
xaminer ADEMAR	Document Number	Date	Name Vuon et al.			C.	-3-1
ΛΛ	5,343.063	8/30/94	Yuan et al.		1	节星	CENED 24 203
AB	5,426,605	6/20/95	Van Berkel et al.			1	22 11
AC AC	5,436,481	7/25/95	Egawa et al.			000	10
AD	B1 5,172,338	7,8/97	Mehrotra et al.			LEW	2.800
AE	5,661,053	8/26/97	Yuan			TEO	7.85
AE AF	5,712,180	1/27/98	Guterman et al.		+	TK C	
AG	7:0.102	6/16/98	Eitan				ं । ।
A) AG		12/22/98	Lin et al.		-	(I - 1)	975 V
Al	725	1/4/00	Eitan		-	1 1	5
A	170,071	2/29/00	Eitan				は _は _し
A		7/18/00	Cernea et al.			780	
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	AL OTHER	ART (Includin	ng Author, Title, Date,	Pertinent Pag	OS Devices "	IEEE Tra	ansactions on
	M Fitan et al "I		Ovide II	n n-channer wie	JU 20110031		
/ 4 /							
1	AN D Frohman	Bentchkowsky, A	Applied Physics Letter	rs, Vol. 18, 197	, 1, page, 332.		
0	AN D. Frohman-				argo storogo d	levice." S	Solid-State
1	10 D Purkman	-Bentchkowsky, "	"FAMOS - A new sen	niconductor ch	arge storage (,,oo, <u> </u>	
2	AO D. Frohman- Electron., 19	974, vol. 17. P. 51	17		1 01 100	16 nn 160	9-172.
A STATE OF THE STA		"Multilevel flach	cells and their trade-c	offs," <u>IEDM To</u>	ech. Dig., 199	70, pp. 10	-
	AP Eitan et al.,	WILLIAM THE STREET				tod	re lines." IDFN
7/2		-4 al - wo 12 N	MONOS single transis 98.	stor memory ce	ell with separa	ated sourc	CC 111103, 111111
2-	AQ 1. Fujiwara	et al., "0.13 um i , 1998, pp. 995-99	98.				
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170	AA	6.103.573	8/15/00	Harari et al.		— ;	F 9			
1	AB	6,104,072	8/15/00	Hirota			12 12			
To a	AC	6.137,718	10/24/00	Reisinger		-	1 1 12 1			
	AD	6,151,248	11/21/00	Harari et al.						
1 / 1	AE	US 6,201,282 B1	3/13/01	Eitan			量品			
Ji	AF	US 6,215,148 B1	4/10/01	Eitan			3 7			
	AG	US 6,222,762 B1	4/24/01	Guterman et al.			7 -			
15	AH	US 6,248,633 B1	6/19/01	Ogura, et al.			13 3			
	AI						10 70 T			
	Ai		Foreig	gn Patent Documents			7 Translati			
		Document	Date	Country	Class	Subclass	Yes			
	AJ	OTHER A	RT (Including	g Author, Title, Date, Po	ertinent Pages, l	Etc.)				
Comp	1	- at 1-1	"A new SON	OS memory using sout	rce-side injectio	n for programm	ing," <u>IEEE</u>			
	ΛK	Clastron Device	.ett., voi. 19, 1	990. pp. 200 200						
		D. I. Weight "Three	e-state MNOS	FET memory array." I	BM Technical	Disclosure Bull	etin, vol. 18, no.			
7	AL	1 May 1976, pp. 14	192-1493.							
. 1/	40		1 WA MOSE	ET with Si-implanted (Gate-SiO: Insula	ntor for Nonvola	tile Memory			
4	A.M	Applications	:EE, U-/802-0	017-472 PP						
1.	1			The state of the s	momory using S	Si-rich SiO: injec	tors and a floatir			
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7,	AC	1 Childe to Linders	standing and O	Strig IVV Stri						
A		pp. 9-25.		- Wall III h Coto In	iection Efficien	cv," Internation	al Electronic Dev			
	, Al	Kamiya, M., et	al., "EPROM (F. San Francis	co, California, (Dec. 13	8-15, 1982) pps.	741-744				
1 -4	4	Meeting of IEE								
. //		7 7 2	Date Cor	sidered 1/1/1/k	5					
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U.S. Department of Commerce, Patent and Trademark Office					Atty Docket No. M-12336 US			Application No. 10/002,696	
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RADE			U.S. Pa	atent Documents	±====			7111 D	IC
Examiner		Document Number	Date	Name		Class	Subclass	Filing Date Appropria	
Initial	AA	4,398,248	Aug. 9, 1983	Hsia et al.					
	AB	6,349,062	Feb. 19, 2002	Thurgate					
	AC	6,366,501	Apr. 2, 2002	Thurgate et al.	Thurgate et al.				
<u> </u>	AD	6,406,960	Jun. 18, 2002	Hopper et al.		<u> </u>			
	AE								
	AF								
	AG								
] AG		Foreign	n Patent Docume	nts				
								Translat	
	1	Document	Date	Count	ry	Class	Subclass	Yes	No
	AH	SU 960953 A	23 Sept. 1982	Soviet U	nion	<u> </u>		Abstract	X
0	All								
	AJ	OTHER	ART (Including	Author, Title, Da	ate, Pertir	nent Pages,	Etc.)		
	1 477					ODIA Ca	to Cource Sid	le <u>I</u> njection and	d ONC
177	AK	Charge Storage	OTHER ART (Including Addios, This, Device with SP lit Gate Source Side Injection and ONO Chen, Wei-Ming et al., "A Novel Flash Memory Device with SP lit Gate Source Side Injection and ONO Charge Storage Stack (SPIN)", 1997 Symposium on VLSI Technology Digest of Technical Papers, pp. 63-64. Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, Yakov, et al., "Novel Techniques for Data Retention and Leff Measurements in Two Bit Roizin, The						
1	AL	microFLASH*	Memory Cells", A	AIP Conference	110000	-8-7			
7	AM	Hsia, Yukun, "3303-3308.	Hsia, Yukun, "Memory Applications of the MNOS", Wescon Technical Papers, Volume 16, 1972, pp. 3303-3308.						
Farminar	V - 1	11/1	Date Conside	ered //T/	c L			1'	ah
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TA THADEN	<u> </u>		U.S. Pat	ent Documents					
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing D If Approp		
The state of the s	AA	4,112,507	Sept. 5, 1978	White et al.					
12-	AB	5,887,145	Mar. 23, 1999	Harari et al.					
	AC	6,281,075	Aug. 28, 2001	Yuan et al.					
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		OTHER	ART (Including Au	thor, Title, Date, Per	tinent Pages, E	tc.)		- Maria	
N. V	AM	Hayashi, Yutak Technology Di	ta et al., "Twin MON gest of Technical Pap	OS Cell With Dual Coers, pp. 122-123.	Control Gates",	2000 Symposi	um on VLSI		
	AN								
	AO								
Examiner	<u> </u>		Date Considere	ed /////					

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